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Bulk moduli of PbS_xSe_{1-x}, PbS_xTe_{1-x}, and $PbSe_xTe_{1-x}$ from the combination of the $cB\Omega$ model with the modified Born theory compared to generalized gradient approximation.

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Abstract

The bulk moduli of PbS_xSe_{1-x}, PbS_xTe_{1-x}, and $PbSe_xTe_{1-x}$ have been recently determined [E. Skordas, Materials Science in Semiconductor Processing 43 (2016) 6568] by employing a thermodynamical model, the so called $cB\Omega$ model, which has been found to give successful results in several applications of defects in solids. Here, we suggest an alternative procedure for this determination which combines the $cB\Omega$ model with the modified Born theory. The results are in satisfactory agreement with those deduced independently by the generalized gradient approximation approach.

Keywords: Bulk modulus, Lead chalcogenides, Generalized gradient approximation, Thermodynamical $cB\Omega$ model

1. Introduction

Since small fundamental energy band gap[1, 2] exists in lead chalcogenides semiconductors of rocksalt structure, it makes them very useful in optoelectronic equipment, including lasers and detectors[3, 4, 5, 6], and very promising for the photoinduced nonlinear optics[7, 8]. Thus, they have attracted a major interest and have been studied by various theoretical techniques[9, 10, 11]. In this frame,

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the structural, electronic and optical properties of PbS_xSe_{1-x}, PbS_xTe_{1-x}, and $PbSe_xTe_{1-x}$ ternary alloys have been studied recently for $x = 0.25, 0.5, 0.75$ and 1.00 by Naeemullah et al. [12] by using the first-principle technique of full-potential linearized augmented plane-wave (FP-LAPW) method with Wu-Cohen generalized gradient approximation (GGA) [13] to solve Kohn-Sham equation[14]. In particular, concerning the structural properties Naeemullah et al. [12] calculated the equilibrium lattice constant (a), the bulk modulus (B), and the pressure derivative of the bulk modulus ($\frac{dB}{dP}$) at the aforementioned compositions. In our previous publication[15], focusing on the variation of B versus the composition, the above GGA results were compared with those obtained on the basis of a thermodynamical model, termed $cB\Omega$ model[16] (see also below), which has been applied for the formation and migration of defects to a variety of solids including several recent applications in semiconductors. Here, we extend our previous study and discuss an alternative procedure to determine B versus the composition in the aforementioned semiconductors' alloys, which combines the thermodynamical $cB\Omega$ model with the modified Born theory of solids [17].

2. The alternative procedure for the determination of the compressibility of PbS_xSe_{1-x}, PbS_xTe_{1-x}, and $PbSe_xTe_{1-x}$

Let us explain how the compressibility κ of a solid solution $A_{1-x}B_x$ is interrelated with compressibilities of the two end members A and B by following Refs. [16, 18]. We call the two end members A and B as pure components 1 and 2, respectively, and label v_1 the volume per atom of the pure component 1 and v_2 the volume per atom of the pure component 2. Let V_1 and V_2 denote the corresponding molar volumes, i.e. $V_1 = Nv_1$ and $V_2 = Nv_2$ (where N stands for Avogadro's number) and assume that $v_1 < v_2$. We now define a "defect volume" [16, 18] as the increase of the volume V_1 if one atom of type 1 is replaced by one atom of type 2. It is now evident that the addition of one "atom" of type 2 to a crystal containing atoms of type 1 will increase its volume by $v_d + v_1$ (see

pp.325 and 326 of Ref. [16]). Assuming that v^d is independent of composition, the volume V_{N+n} of a crystal containing N atoms of type 1 and n atoms of type 2 can be written as

$$V_{N+n} = Nv_1 + n(v^d + v_1) \Longleftrightarrow V_{N+n} = \left[1 + \frac{n}{N}\right] V_1 + nv^d. \tag{1}$$

The molar fraction x is connected to n/N by (see Eq.(12.5) on p.328 of Ref.[16])

$$\frac{n}{N} = \frac{x}{1-x}. \tag{2}$$

The compressibility κ of the solid solution (as well as its bulk modulus $B = 1/\kappa$) can be found by differentiating Eq.(1) with respect to pressure, which finally gives:

$$\kappa V_{N+n} = \kappa_1 V_1 + \frac{n}{N}\left[\kappa^d N v^d + \kappa_1 V_1\right], \tag{3}$$

where κ^d denotes the compressibility of the volume v^d, defined as

$$\kappa^d \equiv \frac{1}{B^d} = -\frac{1}{v^d}\left(\frac{\partial v^d}{\partial P}\right)_T. \tag{4}$$

The "defect volume" v^d can be approximated by (see p.342 of Ref.[16])

$$v^d = \frac{V_2 - V_1}{N} \Longleftrightarrow v^d = v_2 - v_1. \tag{5}$$

The quantity V_{N+n} can be obtained versus the composition by means of Eq.(1) when considering also Eq.(5) and then, the compressibility κ can be studied versus the composition from Eq.(3) by making the crucial assumption that κ^d is independent of composition. An estimation of κ^d can be made by employing the aforementioned thermodynamical model[19, 20, 21] (for a review see Ref.[16]) for the formation and migration of the defects in solids (cf. the replacement of a host atom with a "foreign" one can be considered in general as a defect [22]). This model has been successfully applied, as mentioned, to various categories of solids including diamond[23], fluorides[24, 25, 26, 27], semiconductors[28], mixed alkali halides[29, 30, 31, 32] as well as in complex ionic materials under uniaxial stress that emit electric signals before fracture[33, 34], which is reminiscent of the electric signals observed before major earthquakes[35,

36, 37, 38, 39, 40, 41, 42]. This thermodynamical model states that the defect Gibbs energy g is proportional to the bulk modulus as well as to the mean volume per atom. We then obtain the defect volume $v[=(\partial g/\partial P)_T]$, and therefrom the compressibility κ^d (see Eq.(8.31) on p.156 of Ref.[16]) is found to be

$$\kappa^d = \frac{1}{B} - \frac{\left(\frac{\partial^2 B}{\partial P^2}\right)_T}{\left(\frac{\partial B}{\partial P}\right)_T - 1}, \tag{6}$$

where the quantity $\left(\frac{\partial^2 B}{\partial P^2}\right)_T$ can be approximated from the modified Born theory[17] according to

$$\left(\frac{\partial^2 B}{\partial P^2}\right)_T = -\frac{4}{9}\frac{(n^B+3)}{B} \tag{7}$$

where n^B is the usual Born exponent. Upon inserting Eq.(7) into Eq.(6) we find κ^d which can be replaced in Eq.(3) leading to

$$\kappa = \kappa_1 \left\{ \frac{V_1}{V_{N+n}} \frac{(N+n)}{N} + \frac{n}{N}\frac{Nv^d}{V_{N+n}} \left[1 + \frac{4}{9}\frac{(n^B+3)}{(\frac{dB_1}{dP}-1)}\right]\right\}. \tag{8}$$

By taking into account that within Born approximation $\frac{dB_1}{dP}$ is given by[16, 17]

$$\frac{dB_1}{dP} = \frac{n^B+7}{3}, \tag{9}$$

we obtain

$$\kappa = \kappa_1 \left\{ \frac{V_1}{V_{N+n}} \frac{(N+n)}{N} + \frac{n}{N}\frac{Nv^d}{V_{N+n}} \left[1 + \frac{4}{3}\frac{(n^B+3)}{(n^B+4)}\right]\right\}. \tag{10}$$

Using now Eq.(5), we have

$$\kappa = \kappa_1 \left\{ \frac{V_1}{V_{N+n}} \frac{(N+n)}{N} + \frac{n}{N}\frac{(V_2-V_1)}{V_{N+n}} \left[1 + \frac{4}{3}\frac{(n^B+3)}{(n^B+4)}\right]\right\}, \tag{11}$$

which upon substituting $v_{N+n} = v_{N+n}/(N+n)$ leads to

$$\kappa = \kappa_1 \left\{ \frac{v_1}{v_{N+n}} + \frac{n}{n+N}\frac{(v_2-v_1)}{v_{N+n}} \left[1 + \frac{4}{3}\frac{(n^B+3)}{(n^B+4)}\right]\right\} \tag{12}$$

or

$$B = B_1 \left\{ \frac{v_1}{v_{N+n}} + x\frac{(v_2-v_1)}{v_{N+n}} \left[1 + \frac{4}{3}\frac{(n^B+3)}{(n^B+4)}\right]\right\}^{-1} \tag{13}$$

by virtue of Eq.(2) and the definitions of the compressibilities κ and κ_1.

Using Eq.(13) and the values of B_1, v_1, v_2 and n^B, e.g., $n^B = 10.5$ for PbS and $n^B = 11.0$ for PbSe (see p.30 of Ref.[43]; see also Fig.5-4 of Anderson [44]), we can estimate B as a function of the composition x. Adopting the stoichiometric notation $PbS_{1-x}Se_x$, $PbS_{1-x}Te_x$, and $PbSe_{1-x}Te_x$ we can compare the results of Eq.(13) with those obtained by GGA [12]. Such a comparison is shown in Fig.1, an inspection of which reveals more or less a satisfactory agreement especially if one considers the following difference between the procedure presented here from the one suggested by Skordas [15]: Within the frame of the procedure followed in our previous paper, which is based solely on the thermodynamical model, in order to determine the bulk modulus of the alloy at a certain composition, one needs the bulk moduli of both end members, while in the frame of the present procedure, which in addition makes use of the modified Born theory, one needs only the bulk modulus of the end member that has the smaller mean volume per atom.

3. Conclusions

By combining the thermodynamical $cB\Omega$ model with the modified Born theory of solids, a procedure is proposed which enables the computation of the bulk moduli of the semiconductors' alloys $PbS_{1-x}Se_x$, $PbS_{1-x}Te_x$, and $PbSe_{1-x}Te_x$ at various compositions. Interestingly, the results are compatible with those that have been recently deduced by tedious GGA calculations.

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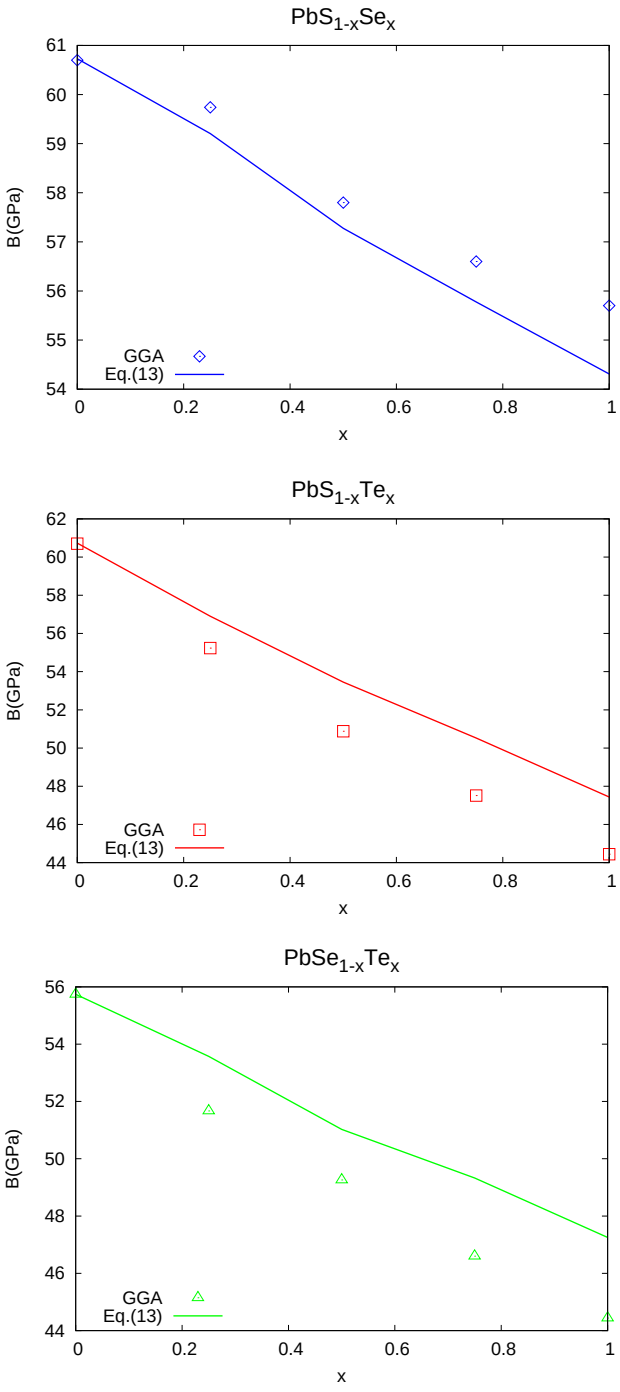

Figure 1: Bulk modulus versus composition. The continous curve results from the present procedure, i.e., Eq.(13), while the open symbols have been obtained by GGA.

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